

IGBT Trench Module

$$V_{CES} = 1700 \text{ V}$$

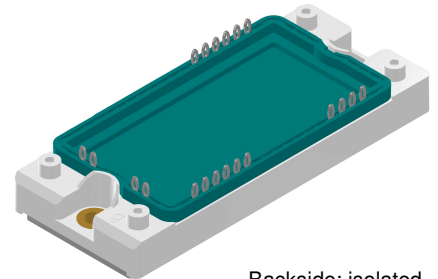
$$I_{C25} = 400 \text{ A}$$

$$V_{CE(sat)} = 2 \text{ V}$$

Boost/Brake Chopper + free wheeling Diode + NTC

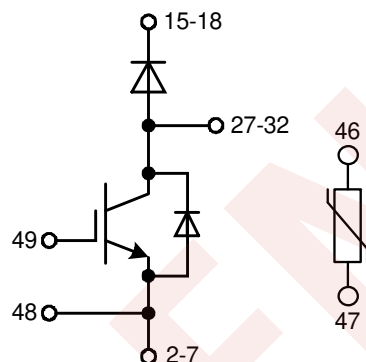
Part number

MITA300RF1700PTD



Backside: isolated

 E72873



Features / Advantages:

- Brake with Infineon IGBT³

Applications:

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipment
- Switched-mode and resonant-mode power supplies
- Inductive heating, cookers
- Pumps, Fans

Package: E2-Pack

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- PressFit-Pins for PCB mounting
- Height: 17 mm
- Base plate: Copper internally DCB isolated
- Advanced power cycling
- Phase Change Material available

Terms and Conditions of Usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

- to perform joint risk and quality assessments;

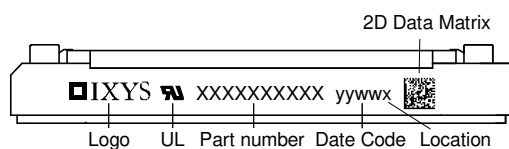
- the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

Free Wheeling Diode FWD				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1700	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1700	V
I_R	reverse current, drain current	$V_R = 1700\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			100	μA
	* not applicable, see I_{ces} at IGBT	$V_R = 1700\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$			0.8	mA
V_F	forward voltage drop	$I_F = 40\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			2.20	V
		$I_F = 80\text{ A}$				2.75	V
		$I_F = 40\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			2.30	V
		$I_F = 80\text{ A}$				3.15	V
I_{FAV}	average forward current	$T_C = 80^{\circ}\text{C}$ rectangular $d = 0.5$	$T_{VJ} = 150^{\circ}\text{C}$			40	A
V_{F0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}\text{C}$			1.35	V
r_F	slope resistance					23	m Ω
R_{thJC}	thermal resistance junction to case					1	K/W
R_{thCH}	thermal resistance case to heatsink				0.30		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$			125	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$	$T_{VJ} = 45^{\circ}\text{C}$			300	A
C_J	junction capacitance	$V_R = 900\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		14		pF

Boost IGBT				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{CES}	collector emitter voltage	T _{VJ} = 25°C				1700	V
V _{GES}	max. DC gate voltage					±20	V
V _{GEM}	max. transient gate emitter voltage					±30	V
I _{C25}	collector current	T _C = 25°C				400	A
I _{C80}		T _C = 80°C				280	A
P _{tot}	total power dissipation	T _C = 25°C				1390	W
V _{CE(sat)}	collector emitter saturation voltage	I _C = 300A; V _{GE} = 15 V	T _{VJ} = 25°C		2	2.45	V
			T _{VJ} = 125°C		2.4		V
V _{GE(th)}	gate emitter threshold voltage	I _C = 12mA; V _{GE} = V _{CE}	T _{VJ} = 25°C	5.2	5.8	6.4	V
I _{CES}	collector emitter leakage current	V _{CE} = V _{CES} ; V _{GE} = 0 V	T _{VJ} = 25°C			1.2	mA
			T _{VJ} = 125°C		1.4		mA
I _{GES}	gate emitter leakage current	V _{GE} = ±20 V				800	nA
Q _{G(on)}	total gate charge	V _{CE} = 900 V; V _{GE} = 15 V; I _C = 300 A			3400		nC
t _{d(on)}	turn-on delay time	inductive load V _{CE} = 900 V; I _C = 300 A V _{GE} = ±15 V; R _G = 4.7 Ω	T _{VJ} = 125°C		340		ns
t _r	current rise time				90		ns
t _{d(off)}	turn-off delay time				800		ns
t _f	current fall time				400		ns
E _{on}	turn-on energy per pulse				100		mJ
E _{off}	turn-off energy per pulse				75		mJ
RBSOA	reverse bias safe operating area	V _{GE} = ±15 V; R _G = 4.7 Ω	T _{VJ} = 125°C				
I _{CM}		V _{CEmax} = 1700 V				600	A
SCSOA	short circuit safe operating area	V _{CEmax} =1700 V					
t _{SC}	short circuit duration	V _{CE} = 900 V; V _{GE} = ±15 V	T _{VJ} = 125°C			10	μs
I _{SC}	short circuit current	R _G = 4.7 Ω; non-repetitive			1600		A
R _{thJC}	thermal resistance junction to case					0.09	K/W
R _{thCH}	thermal resistance case to heatsink				0.03		K/W
Boost Diode BD							
V _{RRM}	max. repetitive reverse voltage	T _{VJ} = 25°C				1700	V
I _{F25}	forward current	T _C = 25°C				400	A
I _{F80}		T _C = 80°C				300	A
V _F	forward voltage	I _F = 300A	T _{VJ} = 25°C			2.20	V
			T _{VJ} = 125°C		2.00		V
I _R	reverse current	V _R = V _{RRM}	T _{VJ} = 25°C			1.2	mA
			T _{VJ} = 125°C		1.2		mA
Q _{rr}	reverse recovery charge	V _R = 900 V -di _F /dt = 3000 A/μs I _F = 300A; V _{GE} = 0 V	T _{VJ} = 125°C		80		μC
I _{RM}	max. reverse recovery current				300		A
t _{rr}	reverse recovery time				950		ns
E _{rec}	reverse recovery energy				40		mJ
R _{thJC}	thermal resistance junction to case					0.14	K/W
R _{thCH}	thermal resistance case to heatsink				0.05		K/W

Package E2-Pack				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal				30	A
T_{VJ}	virtual junction temperature			-40		150	°C
T_{op}	operation temperature			-40		125	°C
T_{stg}	storage temperature			-40		125	°C
Weight					176		g
M_D	mounting torque			3		6	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal		6.0			mm
$d_{Spb/Apb}$		terminal to backside		12.0			mm
V_{ISOL}	isolation voltage	t = 1 second t = 1 minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	3600 3000			V V
$R_{pin-chip}$	resistance pin to chip	$V = V_{CEsat} + 2 \cdot R \cdot I_C$ resp. $V = V_F + 2 \cdot R \cdot I_F$			2.5		mΩ



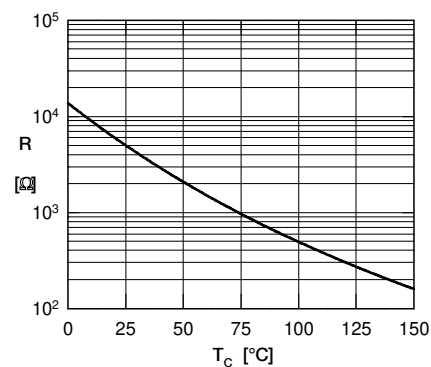
Part description

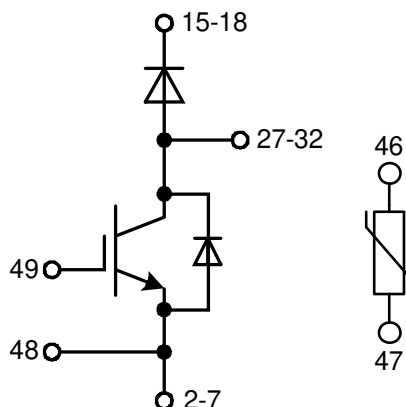
M = Module
 I = IGBT
 T = IGBT Trench
 A = Gen 3 / std
 300 = Current Rating [A]
 RF = Boost/Brake Chopper + free wheeling Diode
 1700 = Reverse Voltage [V]
 PT = PressFit-Pin, Thermistor
 ED = E2-Pack
 - = Hyphen
 PC = Phase Change Material

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MITA300RF1700PTED	MITA300RF1700PTED	Blister	28	516670
Alternative	MITA300RF1700PTED-PC	MITA300RF1700PTED	Blister	28	515402

Temperature Sensor NTC

Symbol	Definition	Conditions	min.	typ.	max.	Unit
R_{25}	resistance	$T_{VJ} = 25^\circ$	4.85	5	5.15	kΩ
$B_{25/50}$	temperature coefficient			3375		K





Boost IGBT

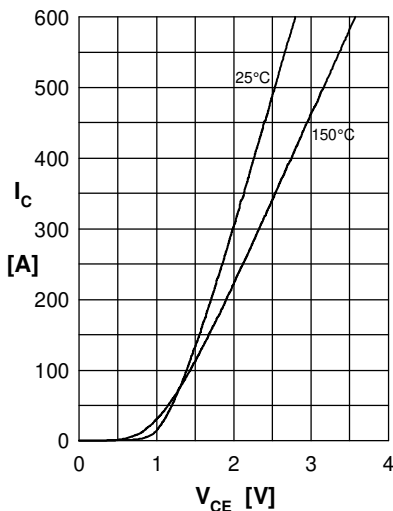


Fig.1 Typ. output characteristics IGBT

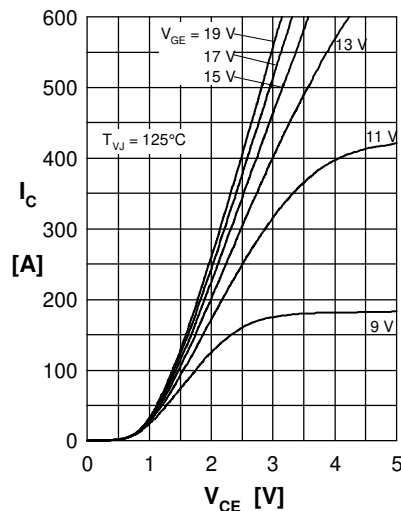


Fig.2 Typ. output characteristics IGBT

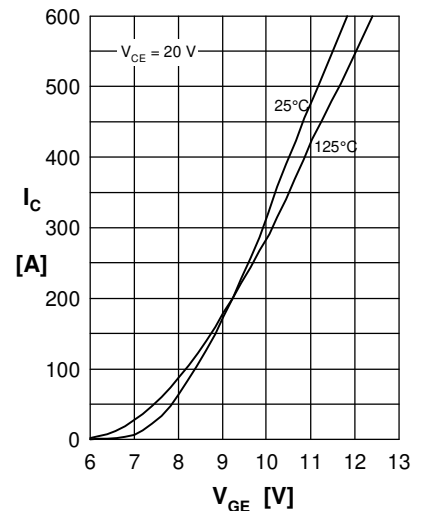


Fig.3 Typ. transfer charact. IGBT

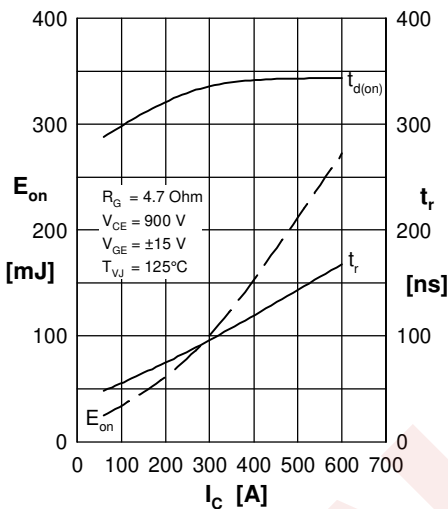


Fig.4 Typ. turn-on energy & switch. times vs. collector current

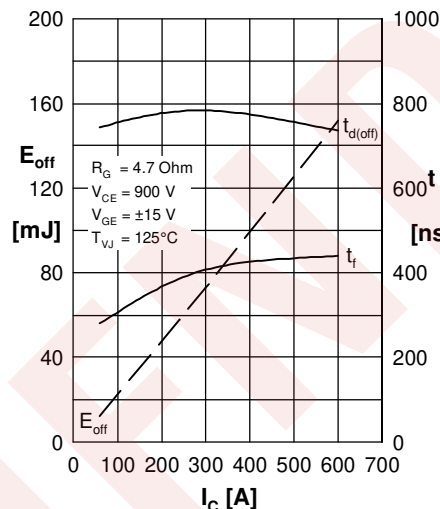


Fig.5 Typ. turn-off energy & switch. times vs. collector current

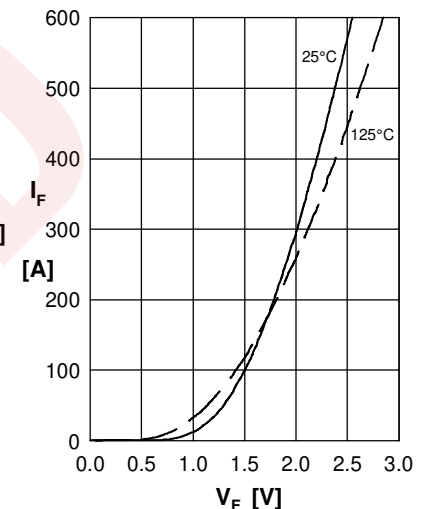


Fig.6 Typ. forward characteristics Diode

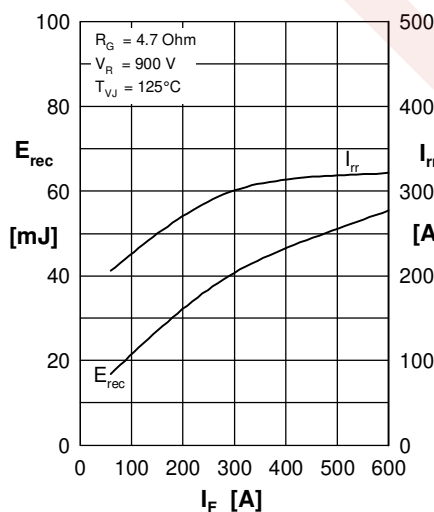


Fig.7 Typ. reverse recovery characteristics Diode

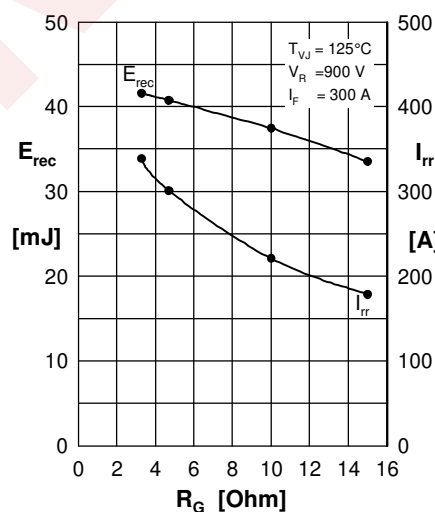


Fig.8 Typ. reverse recovery characteristics Diode

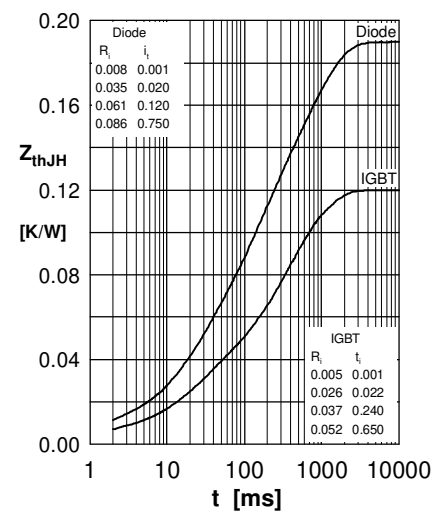


Fig.9 Typ. transient thermal resistance junction to heatsink